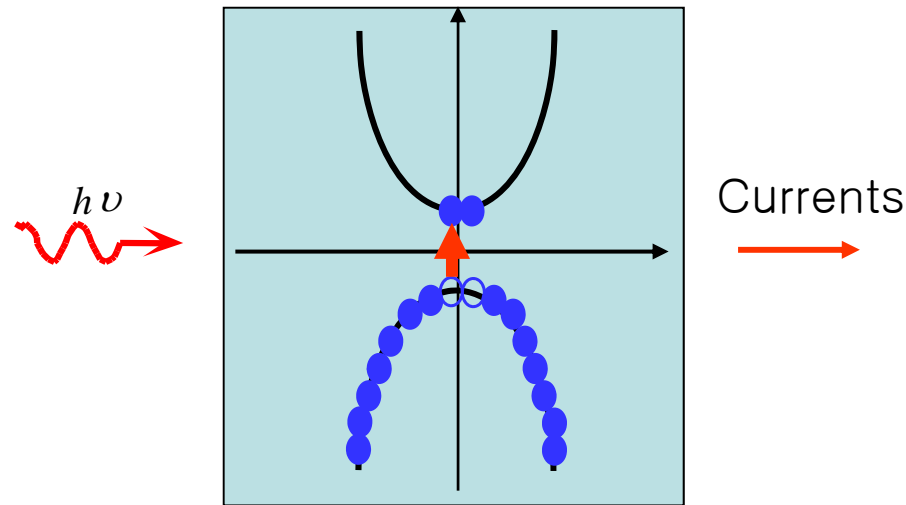


# Lect. 26: Photodetectors

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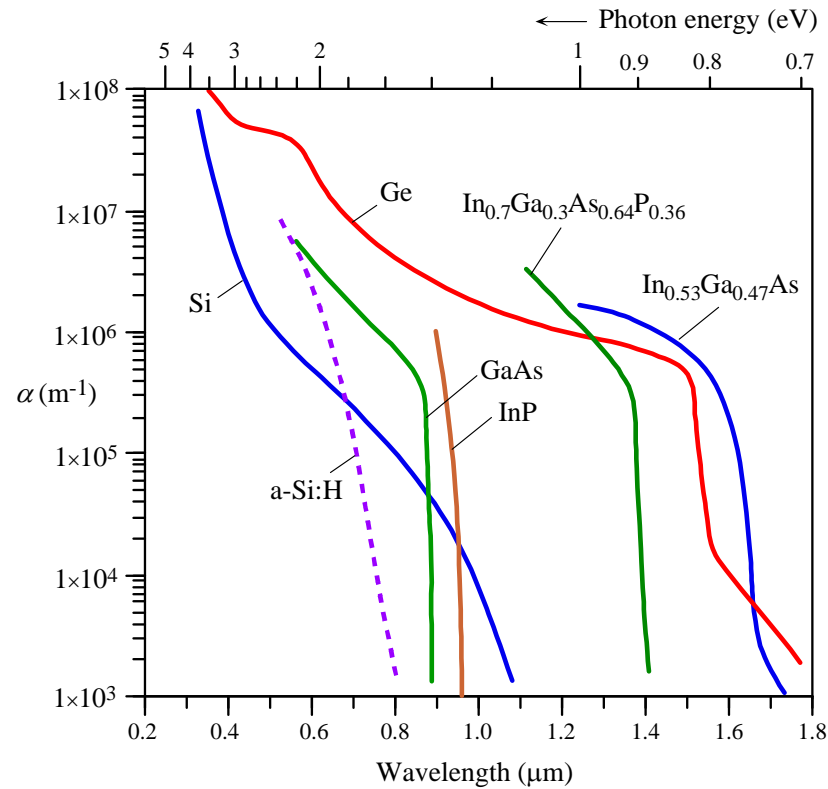
Photodetection: Absorption  $\Rightarrow$  Current Generation



Materials for photodetection:  $E_g < h\nu$

Various methods for generating currents with photo-generated carriers:  
photoconductors, photodiodes, avalanche photodiodes

# Lect. 26: Photodetectors



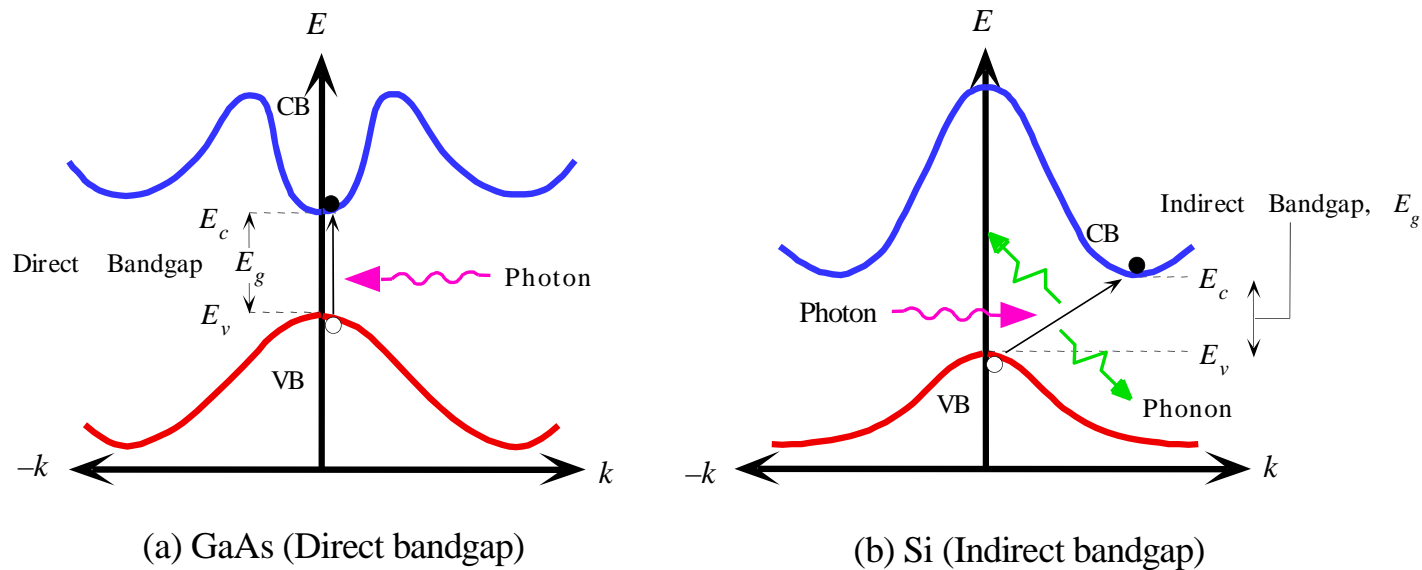
Sharp decrease in absorption for photon energy  $< E_g$

$$P_{\text{out}}/P_{\text{in}} = \exp(gL)$$

$$g < 0 \rightarrow \alpha = -g$$

# Lect. 26: Photodetectors

– Photodetection for indirect bandgap materials



Absorption in indirect bandgap semiconductor is possible

→ Indirect semiconductors (Si) are used for solar cells and image sensors

# Lect. 26: Photodetectors

Photodetection efficiency

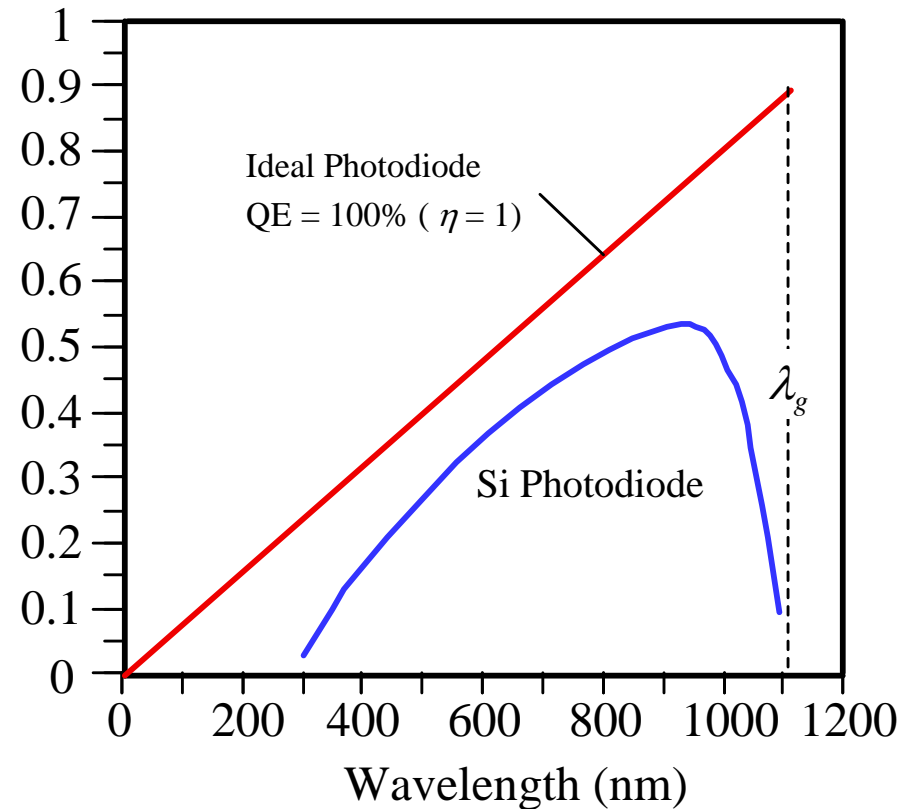
$$R \text{ (Responsivity)} = \frac{I}{P}$$

$$\eta \text{ (Quantum Efficiency)} = \frac{I/q}{P/h\nu}$$

$$R = \eta \cdot \frac{q}{h\nu} \quad h\nu[\text{eV}] = \frac{1.24}{\lambda[\mu\text{m}]}$$

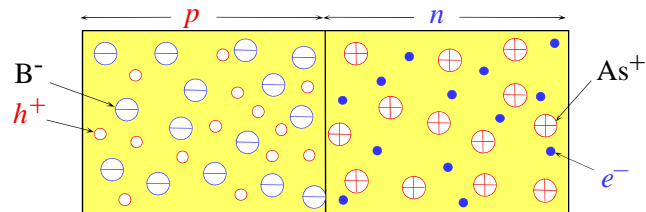
$$R = \eta \cdot q[\text{C}] \cdot \frac{\lambda}{1.24[\text{eV}]} = \eta \cdot \frac{\lambda}{1.24} [\text{1/V}]$$

Responsivity (A/W)



# Lect. 26: Photodetectors

## Photodiodes



PN junction in reverse bias

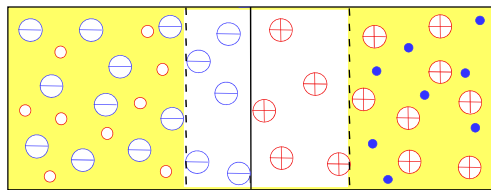
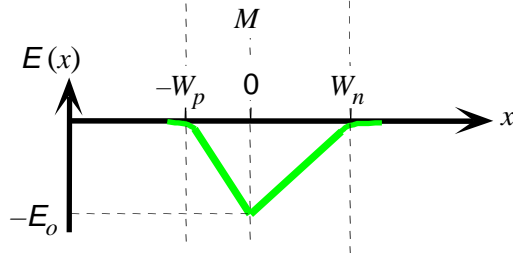


Photo-generated carriers are removed by built-in field in depletion region (space charge region)



# Lect. 26: Photodetectors

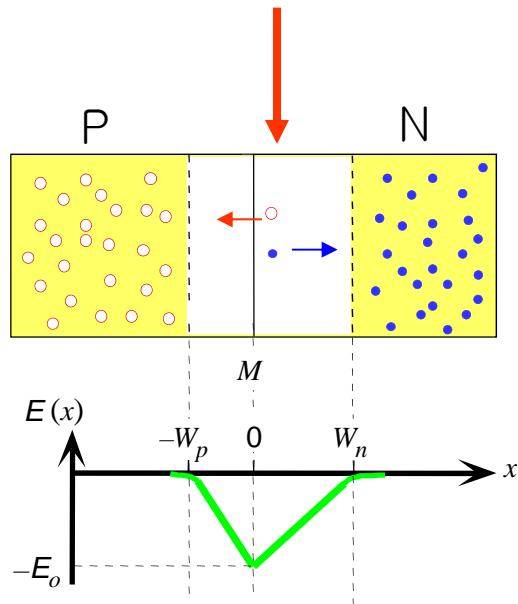


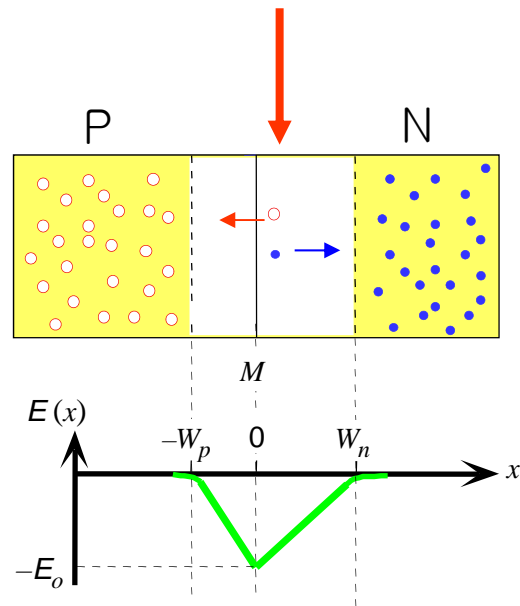
Photo-generated carriers drift into P (holes) and N (electrons) regions generating currents

$$I = \eta_{\text{int}} \frac{P}{h\nu} q$$

One photon creates a pair of electron and hole

# Lect. 26: Photodetectors

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Problem: depletion region is very thin ( $< 1 \mu\text{m}$ )  
 $\rightarrow \eta_{\text{int}}$  is very small

$\Rightarrow$  Use PIN structure

# Lect. 26: Photodetectors

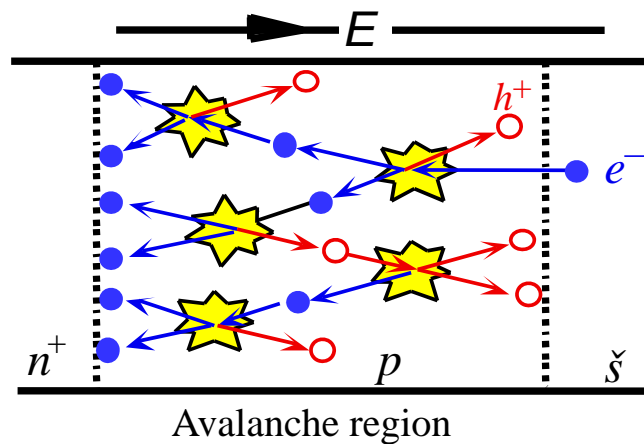
PD with gain?

Avalanche Photodiode (APD)

(avalanche: a large mass of snow, ice, earth, rock, or other material in swift motion down a mountainside)

Achieve gain by multiplying electrons and/or holes.

Impact Ionization: Under high E-field, electrons and holes can have sufficiently high kinetic energies breaking bonds and creating new e-h pairs.

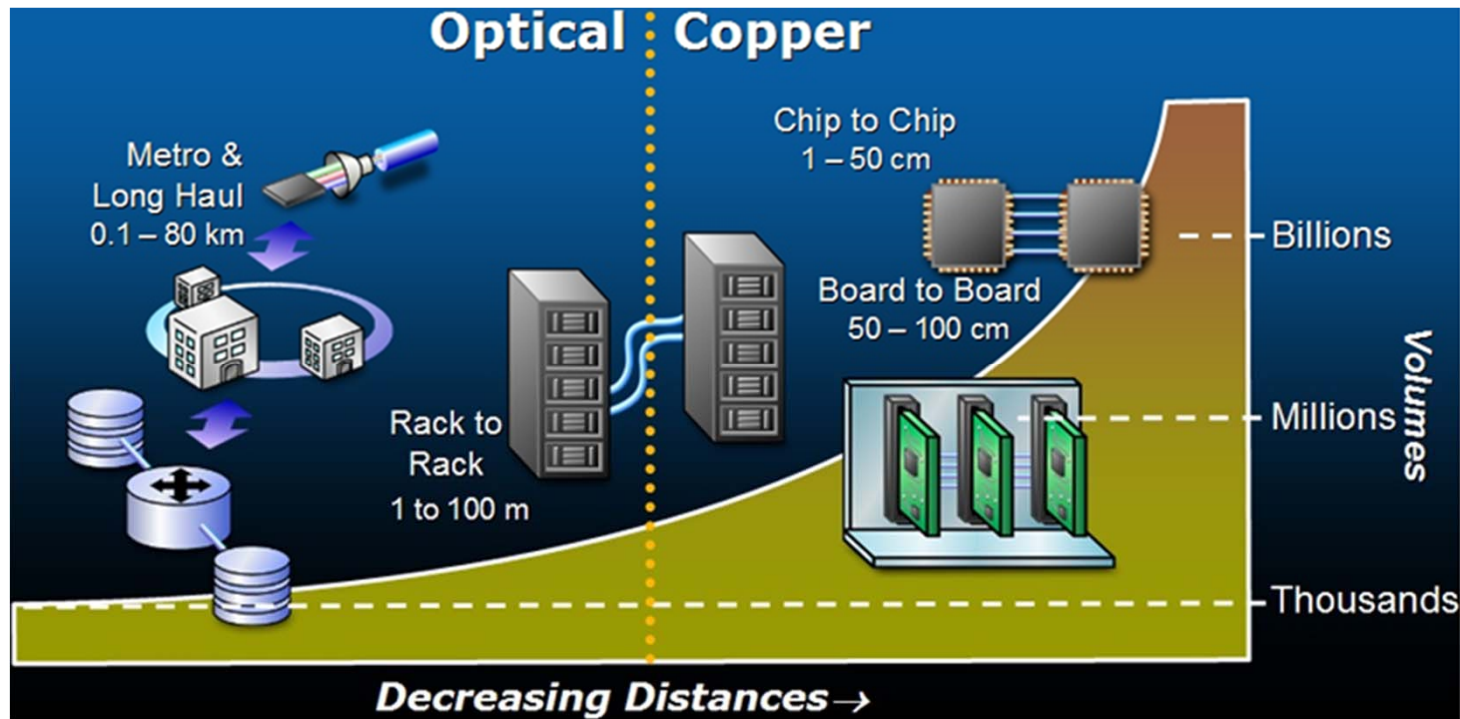


It is preferred only one type of carrier (either electron or hole) causes impact ionization

$\kappa$ : ratio of ionization coefficients  
(= hole/electron)



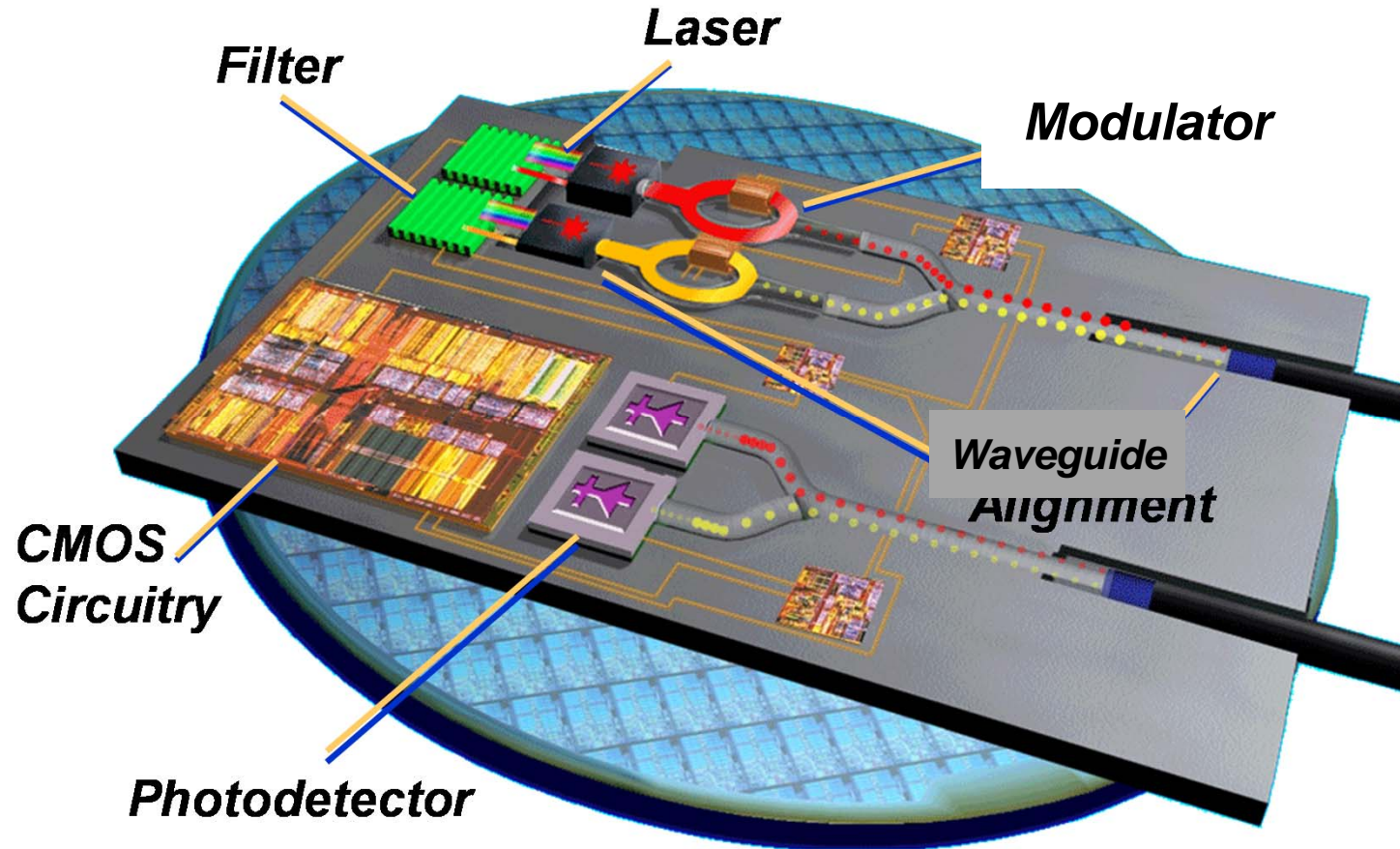
# Current Status of Photonics Technology



- Photonics has been very successful in **Left**
- Photonics has to go to **Right** in order to maintain its growth
- Telecom Operators → Semiconductor Companies
- Data rate, Distance → Data rates, Cost, Power
- There is no better platform than Si

# Ultimate Solution: Si Electronic-Photonic Integration

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If interested, come and see me!